

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	2.0Ω @ V _{GS} = 5.0V	390mA
60V	2.5Ω @ V _{GS} = 2.5V	368mA
	4.0Ω @ V _{GS} = 1.8V	309mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor controls
- Power management functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN62D2UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

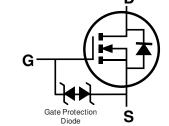
Mechanical Data

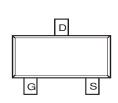
- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe.
 Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.008 grams (Approximate)





SOT23





Top View

Equivalent Circuit

Top View

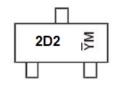
Ordering Information (Note 4)

Part Number	Package	Packing		
Part Number	Fackage	Qty.	Carrier	
DMN62D2UQ-7	SOT23	3,000	Tape & Reel	
DMN62D2UQ-13	SOT23	10,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) Vgs = 5.0V	lo	390 314	mA		
Maximum Continuous Body Diode Forward Current	t (Note 5)	Is	390	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6) (Note 5)		I _{DM}	1.2	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		PD	0.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	238	°C/W
Total Power Dissipation (Note 5)		PD	0.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	197	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

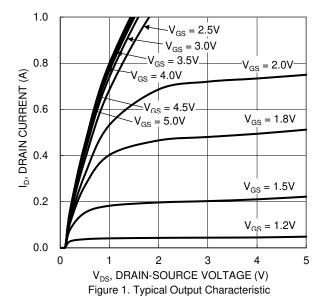
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		•				
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	٧	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1.0	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_		±10	μΑ	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5		1.0	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
			1.0	2.0		V _G S = 5.0V, I _D = 0.05A
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.7	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$
			2.1	4.0		$V_{GS} = 1.8V, I_D = 0.05A$
Diode Forward Voltage	V _{SD}	_	0.7	1.4	٧	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	41	_	pF	
Output Capacitance	Coss	_	5.4	_	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	4.2	_	pF	1 – 1.000112
Gate Resistance	Rg	_	52	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg	_	0.8	_	nC	V 45V V 40V
Gate-Source Charge	Qgs	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V$ $I_{D} = 250mA$
Gate-Drain Charge	Q_{gd}		0.1	_	nC	ID = 250IIIA
Turn-On Delay Time	t _{D(ON)}	_	1.5	_	ns	
Turn-On Rise Time	tR	_	9.7	_	ns	V _{DD} = 30V, V _{GS} = 10V
Turn-Off Delay Time	tD(OFF)	_	22.6	_	ns	$R_G = 25\Omega$, $I_D = 200mA$
Turn-Off Fall Time	t _F	_	19.5	_	ns	

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





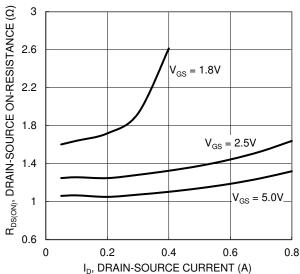


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

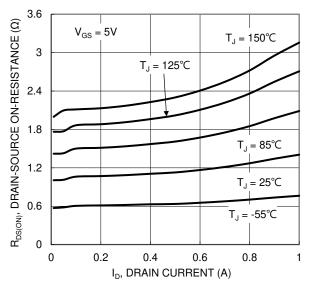


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

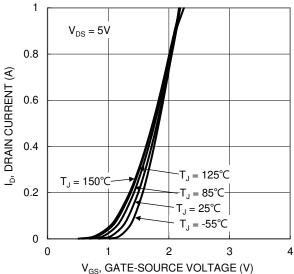
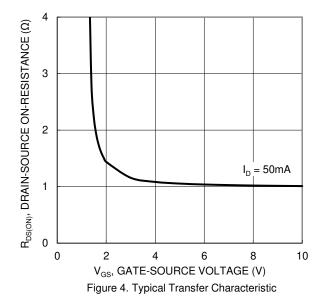


Figure 2. Typical Transfer Characteristic



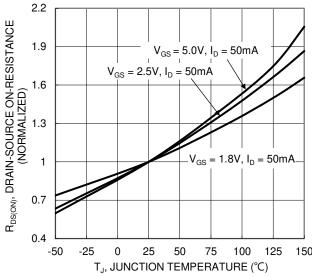


Figure 6. On-Resistance Variation with Junction Temperature



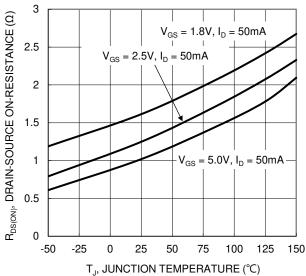


Figure 7. On-Resistance Variation with Junction Temperature

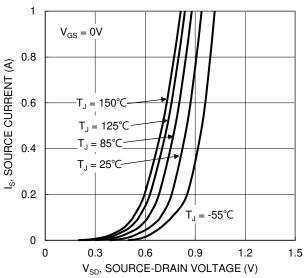


Figure 9. Diode Forward Voltage vs. Current

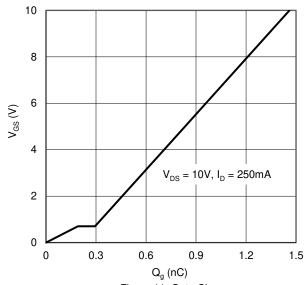


Figure 11. Gate Charge

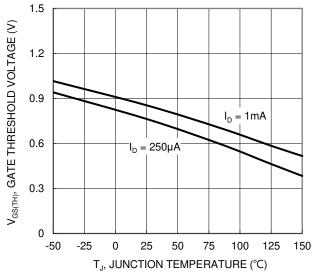
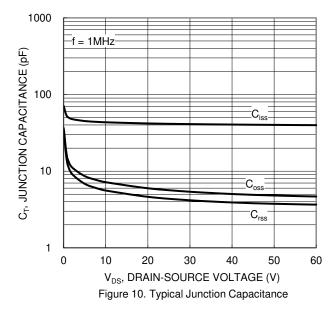


Figure 8. Gate Threshold Variation vs. Junction Temperature



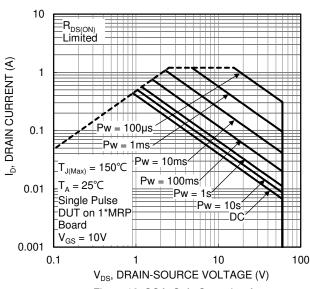


Figure 12. SOA, Safe Operation Area



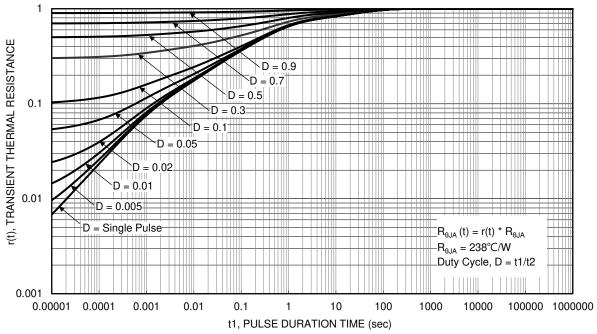


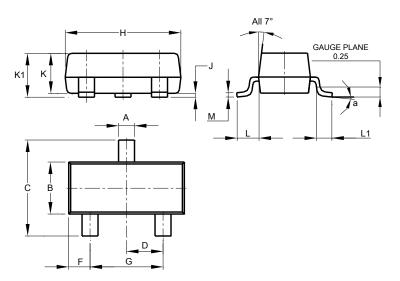
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

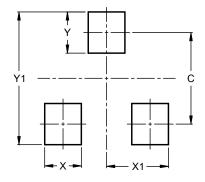


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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